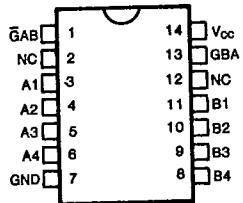


**KS54AHCT 242/243  
KS74AHCT****Quad Bus Transceivers  
with 3-State Outputs****Preliminary Specifications****T-52-31****FEATURES**

- 2-Way Asynchronous Communication Between Data Buses
- Function, pin-out, speed and drive compatibility with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- 3-State outputs with high drive current ( $I_{OL} = 24 \text{ mA} @ V_{OL} = 0.5\text{V}$ ) for direct bus interface
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:  
KS74AHCT: -40°C to +85°C  
KS54AHCT: -55°C to +125°C
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

**PIN CONFIGURATION****DESCRIPTION**

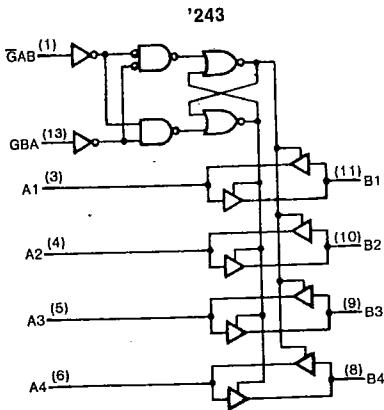
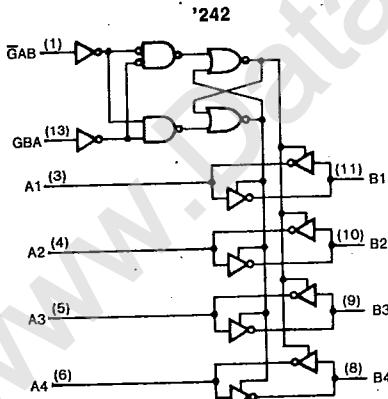
These four-data line transceivers are designed for asynchronous two-way communications between data buses.

These devices provide speeds and drive capability equivalent to their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to V<sub>cc</sub> and ground.

**FUNCTION TABLE**

INPUTS		'242	'243
̄GAB	GBA		
L	L	̄A to B	A to B
H	H	B to A	B to A
H	L	Isolation	Isolation
L	H	Isolation	Isolation

**LOGIC DIAGRAMS**

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**KS54AHCT 242/243  
KS74AHCT****Quad Bus Transceivers  
with 3-State Outputs**

T-52-31

**Absolute Maximum Ratings\***

Supply Voltage Range V <sub>CC</sub> , . . . . .	-0.5V to +7V
DC Input Diode Current, I <sub>IK</sub> (V <sub>I</sub> < -0.5V or V <sub>I</sub> > V <sub>CC</sub> +0.5V) . . . . .	±20 mA
DC Output Diode Current, I <sub>OK</sub> (V <sub>O</sub> < -0.5V or V <sub>O</sub> > V <sub>CC</sub> +0.5V) . . . . .	±20 mA
Continuous Output Current Per Pin, I <sub>O</sub> (-0.5V < V <sub>O</sub> < V <sub>CC</sub> +0.5V) . . . . .	±70 mA
Continuous Current Through V <sub>CC</sub> or GND pins . . . . .	±250 mA
Storage Temperature Range, T <sub>STG</sub> . . . . .	-65°C to +150°C
Power Dissipation Per Package, P <sub>D</sub> † . . . . .	500 mW

\* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

† Power Dissipation temperature derating:

Plastic Package (N): -12mW/°C from 65°C to 85°C  
Ceramic Package (J): -12mW/°C from 100°C to 125°C**Recommended Operating Conditions**

Supply Voltage, V <sub>CC</sub> . . . . .	4.5V to 5.5V
DC Input & Output Voltages*, V <sub>IN</sub> , V <sub>OUT</sub> . . . . .	0V to V <sub>CC</sub>
Operating Temperature	

Range	KS74AHCT: -40°C to +85°C
	KS54AHCT: -55°C to +125°C

Input Rise & Fall Times, t<sub>r</sub>, t<sub>f</sub> . . . . . Max 500 ns\* Unused inputs must always be tied to an appropriate logic voltage level (either V<sub>CC</sub> or GND)**DC ELECTRICAL CHARACTERISTICS** (V<sub>CC</sub>=5V±10% Unless Otherwise Specified)

Characteristic	Symbol	Test Conditions	T <sub>a</sub> = 25°C		KS74AHCT	KS54AHCT	Unit
			Typ	T <sub>a</sub> = -40°C to +85°C	T <sub>a</sub> = -55°C to +125°C	Guaranteed Limits	
Minimum High-Level Input Voltage	V <sub>IH</sub>			2.0	2.0	2.0	V
Maximum Low-Level Input Voltage	V <sub>IL</sub>			0.8	0.8	0.8	V
Minimum High-Level Output Voltage	V <sub>OH</sub>	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub> I <sub>O</sub> =-20μA I <sub>O</sub> =-6mA	V <sub>CC</sub> 4.2	V <sub>CC</sub> -0.1 3.98	V <sub>CC</sub> -0.1 3.84	V <sub>CC</sub> -0.1 3.7	V
Maximum Low-Level Output Voltage	V <sub>OL</sub>	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub> I <sub>O</sub> =20μA I <sub>O</sub> =12mA I <sub>O</sub> =24mA	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V
Maximum Input Current	I <sub>IN</sub>	V <sub>IN</sub> =V <sub>CC</sub> or GND		±0.1	±1.0	±1.0	μA
Maximum 3-State Leakage Current	I <sub>OZ</sub>	Output Enable =V <sub>IH</sub> V <sub>OUT</sub> =V <sub>CC</sub> or GND		±0.5	±5.0	±10.0	μA
Maximum Quiescent Supply Current	I <sub>CC</sub>	V <sub>IN</sub> =V <sub>CC</sub> or GND I <sub>OUT</sub> =0μA		8.0	80.0	160.0	μA
Additional Worst Case Supply Current	ΔI <sub>CC</sub>	per input pin V <sub>I</sub> =2.4V other inputs: at V <sub>CC</sub> or GND I <sub>OUT</sub> =0μA		2.7	2.9	3.0	mA



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**KS54AHCT 242/243**  
**KS74AHCT**

**Quad Bus Transceivers  
with 3-State Outputs**

T-52-31

**AC ELECTRICAL CHARACTERISTICS** (Input  $t_r$ ,  $t_f \leq 2$  ns), AHCT242, AHCT243

Characteristic	Symbol	Conditions <sup>†</sup>	$T_a = 25^\circ C$	KS74AHCT		KS54AHCT		Unit
			$V_{cc} = 5.0V$	$T_a = -40^\circ C$ to $+85^\circ C$	$V_{cc} = 5.0V \pm 10\%$	$T_a = -55^\circ C$ to $+125^\circ C$	$V_{cc} = 5.0V \pm 10\%$	
		Typ	Min	Max	Min	Max		
Propagation Delay, A to B or B to A	$t_{PLH}$	$C_L = 50pF$ $C_L = 150pF$	7 10		11 16		15 21	ns
	$t_{PHL}$	$C_L = 50pF$ $C_L = 150pF$	7 10		11 16		15 21	
Output Enable Time GAB to B, GBA to A	$t_{PZH}$	$R_L = 1k\Omega$ $C_L = 60pF$ $C_L = 150pF$	12 15		20 25		25 21	ns
	$t_{PZL}$	$R_L = 1k\Omega$ $C_L = 50pF$ $C_L = 150pF$	12 15		20 25		25 21	
Output Disable Time, GAB to B, GBA to A	$t_{PHZ}$	$R_L = 1k\Omega$	12		20		25	ns
	$t_{PLZ}$	$C_L = 50pF$	12		20		25	
Input Capacitance	$C_{IN}$		5					pF
Output Capacitance	$C_{OUT}$	Output Disabled	10					pF
Power Dissipation Capacitance*(per stage)	$C_{PD}$	Output Enabled Output Disabled	30 5					pF

\*  $C_{PD}$  determines the no-load dynamic power dissipation:  $P_D = C_{PD} V_{cc}^2 f + I_{cc} V_{cc}$ .

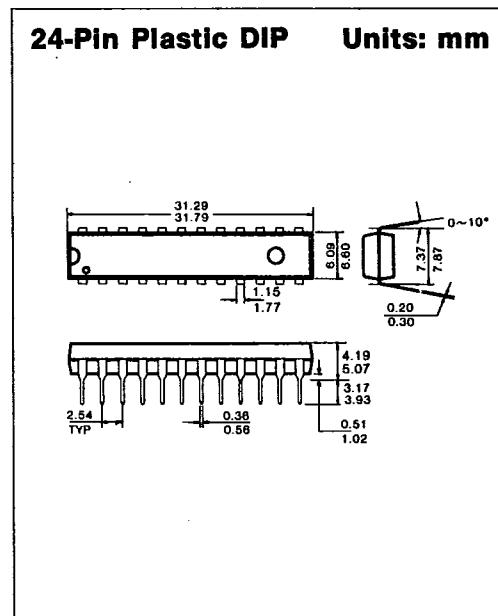
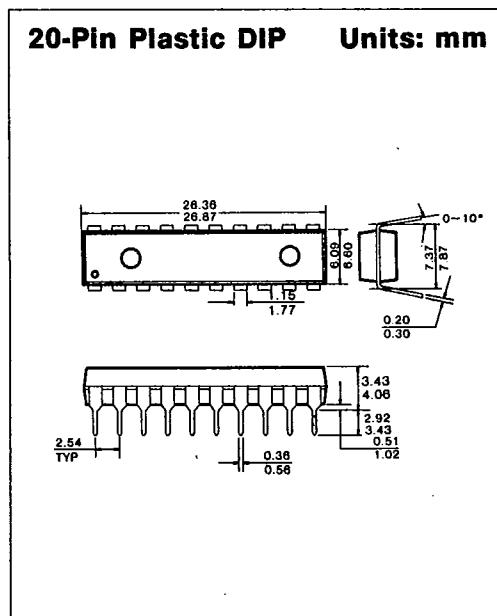
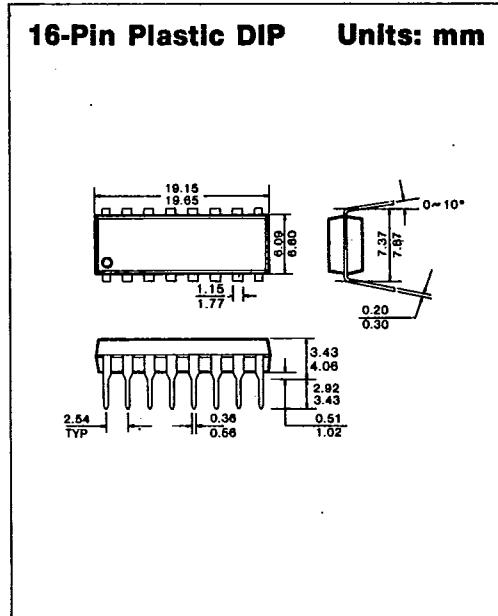
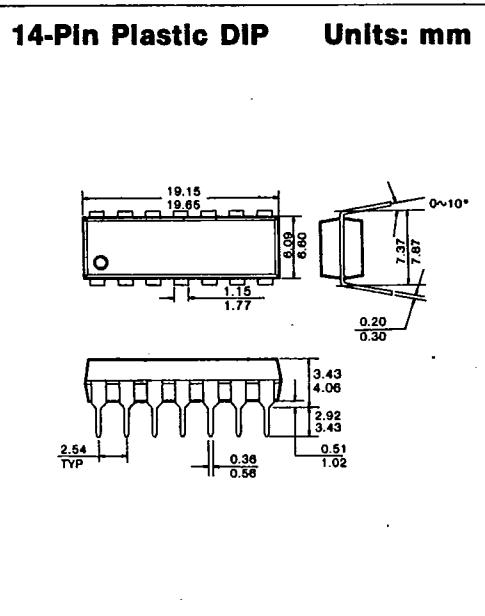
† For AC switching test circuits and timing waveforms see section 2.

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**PACKAGE DIMENSIONS**T-90-20**1. PLASTIC PACKAGES**

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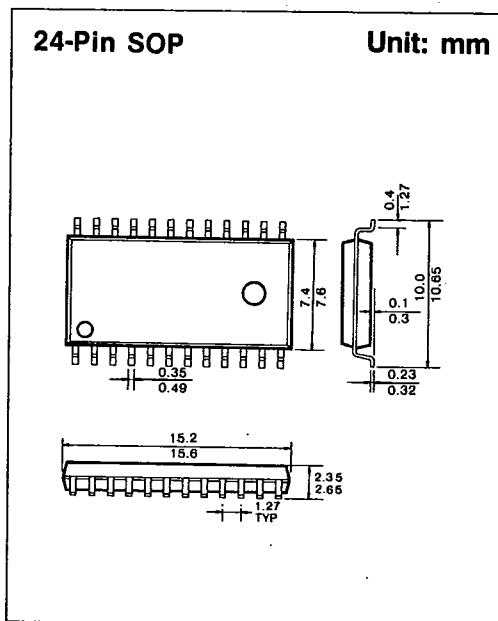
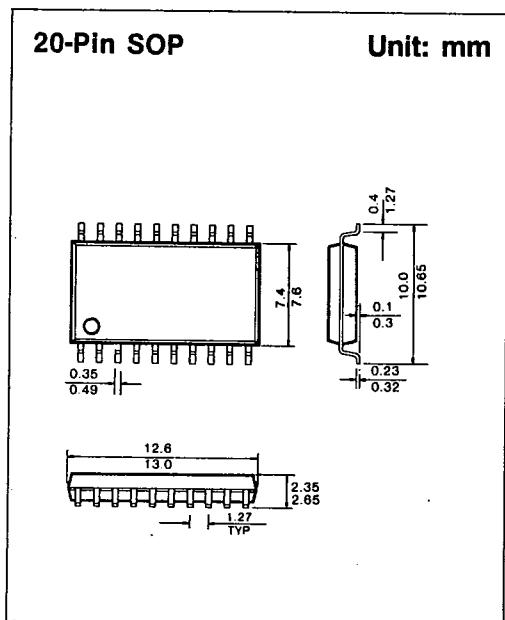
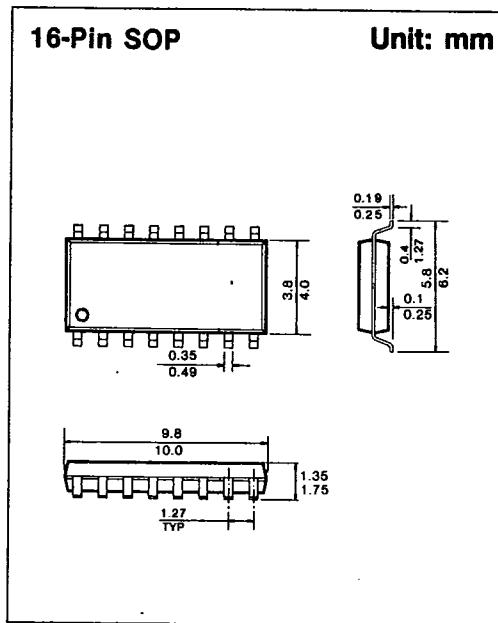
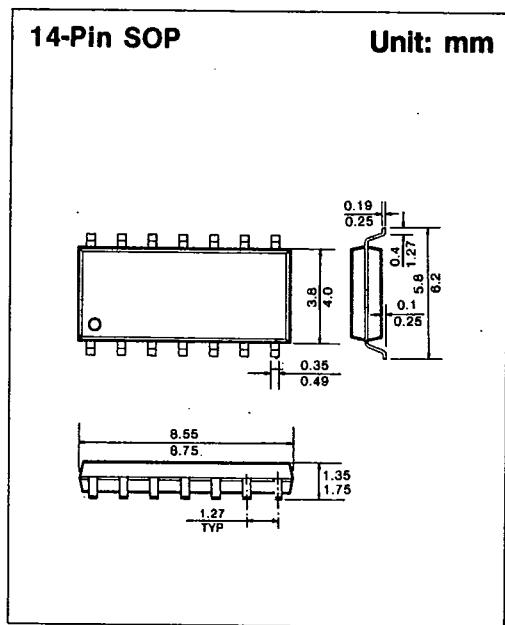


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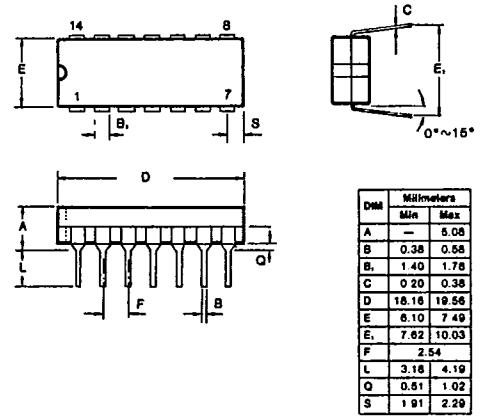
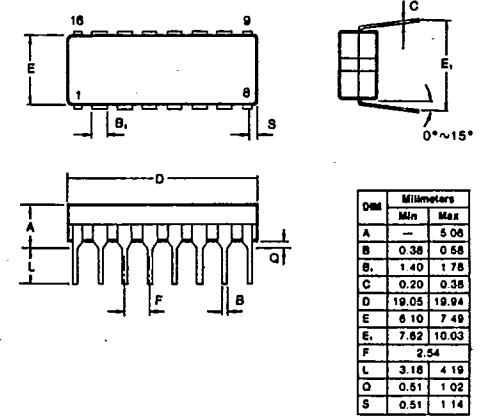
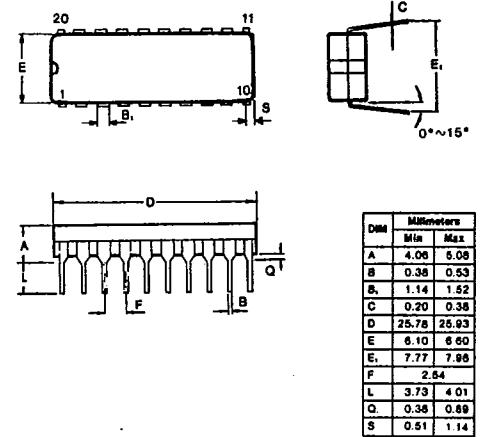
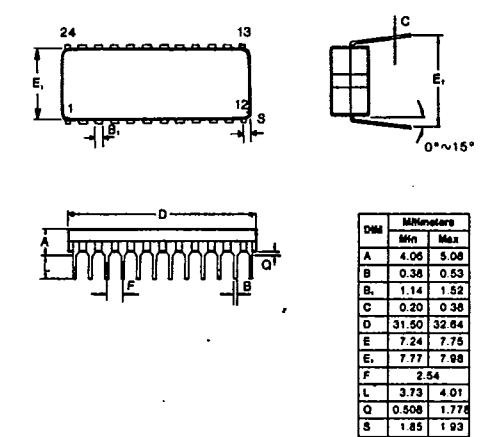
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**PACKAGE DIMENSIONS****T-90-20****SAMSUNG SEMICONDUCTOR**

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**PACKAGE DIMENSIONS**T-90-20**2. CERAMIC PACKAGES****14-Pin Ceramic DIP Units: mm****16-Pin Ceramic DIP Units: mm****20-Pin Ceramic DIP Units: mm****24-Pin Ceramic DIP Units: mm**

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SAMSUNG SEMICONDUCTOR

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